

NPN LOW POWER SILICON TRANSISTOR
Qualified per MIL -PRF -19500/182
Devices
2N720A
**2N1893
2N1893S**
Qualified Level
**JAN
JANTX
JANTXV**
MAXIMUM RATINGS

Ratings	Sy mbol	All Dev ices		Units	
Collector-Emitter Voltage	V_{CEO}	80		Vdc	
Collector-Base Voltage	V_{CBO}	120		Vdc	
Emitter-Base Voltage	V_{EBO}	7.0		Vdc	
Collector-Emitter Voltage ($R_{BE} = 10 \Omega$)	V_{CER}	100		Vdc	
Collector Current	I_C	500		mAdc	
		2N720A	2N1893, S		
Total Power Dissipation	@ $T_A = +25^{\circ}\text{C}$ ⁽¹⁾	P_T	0.5	0.8	W
	@ $T_C = +25^{\circ}\text{C}$ ⁽²⁾		1.8	3.0	
Operating & Storage Junction Temperature Range	T_J, T_{srq}	-65 to +200		$^{\circ}\text{C}$	

THERMAL CHARACTERISTICS

Characteristics	Sy mbol	2N720A	2N1893, S	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	97	58	$^{\circ}\text{C}/\text{W}$

 1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for 2N720A, 4.57 mW/ $^{\circ}\text{C}$ for 2N1893, S $T_A > 25^{\circ}\text{C}$

 2) Derate linearly 10.3 mW/ $^{\circ}\text{C}$ for 2N720A, 17.2 mW/ $^{\circ}\text{C}$ for 2N1893, S $T_C > 25^{\circ}\text{C}$

**TO-18 (TO-206AA)*
2N720A**

**TO-5*
2N1893, 2N1893S**

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Sy mbol	Min.	Max .	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 30 \text{ mAdc}$	$V_{(BR)CEO}$	80		Vdc
Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}, R_{BE} = 10 \Omega$	$V_{(BR)CER}$	100		Vdc
Collector-Base Cutoff Current $V_{CB} = 120 \text{ Vdc}$ $V_{CB} = 90 \text{ Vdc}$	I_{CBO}		10 10	μAdc ηAdc
Emitter-Base Cutoff Current $V_{EB} = 7.0 \text{ Vdc}$ $V_{EB} = 5.0 \text{ Vdc}$	I_{EBO}		10 10	μAdc ηAdc

ELECTRICAL CHARACTERISTICS (con' t)

Characteristics	Sy mbol	Min.	Max .	Unit
ON CHARACTERISTICS ⁽³⁾				
Forward-Current Transfer Ratio I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc}	h _{FE}	20 35 40	120	
Collector-Emitter Saturation Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc}	V _{CE(sat)}		5.0	V _{dc}
Base-Emitter Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc}	V _{BE(sat)}		1.3	V _{dc}

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 50 mA _{dc} , V _{CE} = 10 V _{dc} , f = 20 MHz	h _{fe}	3.0	10	
Small-Signal Short-Circuit Forward Current Transfer Ratio V _{CE} = 5.0 V _{dc} , I _C = 1.0 mA _{dc} V _{CE} = 10 V _{dc} , I _C = 5.0 mA _{dc} , f = 1.0 kHz	h _{fe}	35 45	100	
Small-Signal Short-Circuit Input Impedance V _{CB} = 10 V _{dc} , I _C = 5.0 mA _{dc}	h _{ib}	4.0	8.0	Ω
Small-Signal Short-Circuit Output Admittance V _{CB} = 10 V _{dc} , I _C = 5.0 mA _{dc}	h _{ob}		0.5	μΩ
Output Capacitance V _{CB} = 10 V _{dc} , I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{obo}	2	15	pF

SWITCHING CHARACTERISTICS

Turn-On Time + Turn-Off Time (See Figure 3 of MIL-PRF-19500/182)	t _{on} + t _{off}		30	ηs
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(3) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.